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U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
QVO	A263	5,089,872	02/18/1992	Ozturk et al.			
QVO	A264	5,242,847	09/07/1993	Ozturk et al.			
QVO	A265	5,548,128	08/20/1996	Soref et al.			
QVO	A266	5,607,876	03/04/1997	Biegelsen et al.			
QVO	A267	5,821,577	10/13/1998	Crabbé et al.			

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
QVO	C159	Hamada et al., "A New Aspect of Mechanical Stress Effects in Scaled MOS Devices," <u>IEEE Transactions on Electron Devices</u> , Vol. 38, No. 4 (April 1991), pp. 895-900.
QVO	C160	Huang et al., "Isolation Process Dependence of Channel Mobility in Thin-Film SOI Devices," <u>IEEE Electron Device Letters</u> , Vol. 17, No. 6 (June 1996), pp. 291-293.
QVO	C161	Huang et al., "LOCOS-Induced Stress Effects on Thin-Film SOI Devices," <u>IEEE Electron Device Letters</u> , Vol. 44, No. 4 (April 1997), pp. 646-650.
QVO	C162	Iida et al., "Thermal behavior of residual strain in silicon-on-insulator bonded wafer and effects on electron mobility," <u>Solid-State Electronics</u> , Vol. 43 (1999), pp. 1117-1120.
	C163	International Search Report for Patent Application No. PCT/US 98/19076, dated October 7, 1998, 2 pages.
QVO	C164	Klauk et al., "Thermal stability of undoped strained Si channel SiGe heterostructures," American Institute of Physics, April 1, 1996, pgs. 1975-1977.
QVO	C165	Tiwari et al., "Hole Mobility Improvement in Silicon-on-Insulator and Bulk Silicon Transistors Using Local Strain," <u>IEEE International Electron Devices Meeting Technical Digest</u> , (1997), pp. 939-941.
QVO	C166	Uchino, et al., "A Raised Source/Drain Technology Using In-situ P-doped SiGe and B-doped Si for 0.1-μm CMOS ULSIs," <u>IEEE International Electron Device Meeting Technical Digest</u> , (1997), pp. 479-482.
EXAMINER	Douglas F. Cane	DATE CONSIDERED 2/22/06